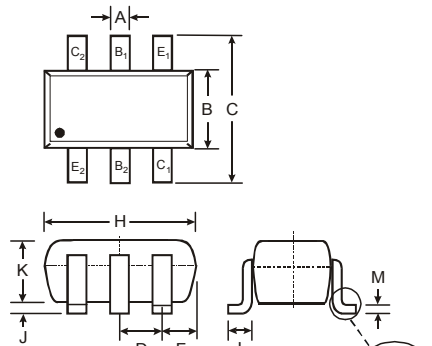


COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR
Features

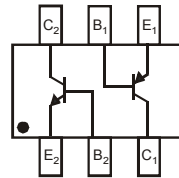
- Complementary Pair
- One 4401-Type NPN,
One 4403-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 4 and 5)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 6
- Ordering & Date Code Information: See Page 6
- Weight: 0.006 grams (approximate)



Note:
 E1, B1, and C1 = PNP 4403 Section,
 E2, B2, and C2 = NPN 4401 Section.
 Type marking indicates orientation



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings, Total Device @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1, 2)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, NPN 4401 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	NPN4401	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I _C	600	mA

Maximum Ratings, PNP 4403 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	PNP4403	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I _C	-600	mA

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Maximum combined dissipation.
 3. No purposefully added lead.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 5. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics, NPN 4401 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	100	nA	V _{CE} = 35V, V _{EB(OFF)} = 0.4V
Base Cutoff Current	I _{BL}	—	100	nA	V _{CE} = 35V, V _{EB(OFF)} = 0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h _{FE}	20 40 80 100 40	— — — 300 —	—	I _C = 100μA, V _{CE} = 1.0V I _C = 1.0mA, V _{CE} = 1.0V I _C = 10mA, V _{CE} = 1.0V I _C = 150mA, V _{CE} = 1.0V I _C = 500mA, V _{CE} = 2.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.40 0.75	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.75 —	0.95 1.2	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}	—	6.5	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{eb}	—	30	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.0	15	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	40	500	—	
Output Admittance	h _{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f _T	250	—	MHz	V _{CE} = 10V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	15	ns	V _{CC} = 30V, I _C = 150mA, V _{BE(off)} = 2.0V, I _{B1} = 15mA
Rise Time	t _r	—	20	ns	V _{CC} = 30V, I _C = 150mA, I _{B1} = I _{B2} = 15mA
Storage Time	t _s	—	225	ns	
Fall Time	t _f	—	30	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.

Electrical Characteristics, PNP 4403 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-40	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-40	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	-100	nA	V _{CE} = -35V, V _{EB(OFF)} = -0.4V
Base Cutoff Current	I _{BL}	—	-100	nA	V _{CE} = -35V, V _{EB(OFF)} = -0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h _{FE}	30 60 100 100 20	— — — 300 —	—	I _C = -100μA, V _{CE} = -1.0V I _C = -1.0mA, V _{CE} = -1.0V I _C = -10mA, V _{CE} = -1.0V I _C = -150mA, V _{CE} = -2.0V I _C = -500mA, V _{CE} = -2.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.40 -0.75	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	-0.75 —	-0.95 -1.30	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}	—	8.5	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{eb}	—	30	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.5	15	kΩ	V _{CE} = -10V, I _C = -1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	60	500	—	
Output Admittance	h _{oe}	1.0	100	μS	
Current Gain-Bandwidth Product	f _T	200	—	MHz	V _{CE} = -10V, I _C = -20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	15	ns	V _{CC} = -30V, I _C = -150mA, V _{BE(off)} = -2.0V, I _{B1} = -15mA
Rise Time	t _r	—	20	ns	
Storage Time	t _s	—	225	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = I _{B2} = -15mA
Fall Time	t _f	—	30	ns	

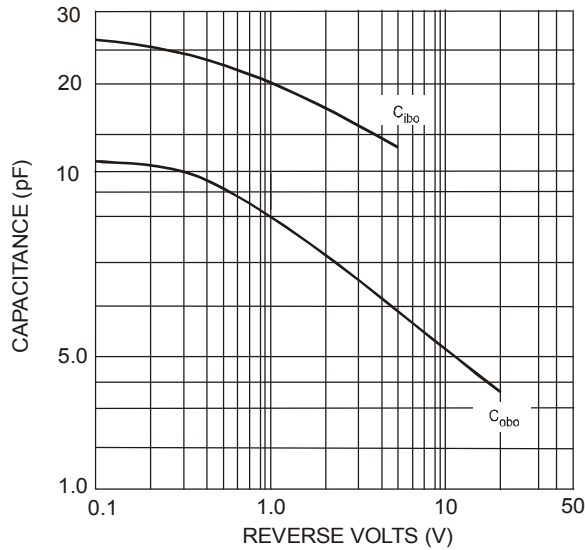


Fig. 1 Typical Capacitance (4401)

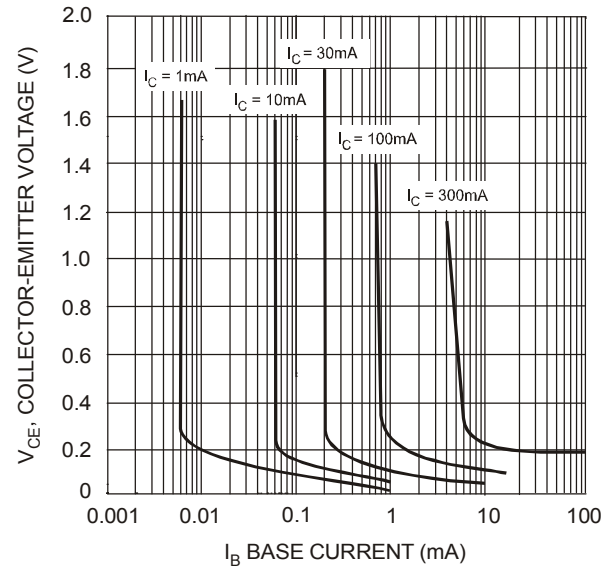


Fig. 2 Typical Collector Saturation Region (4401)

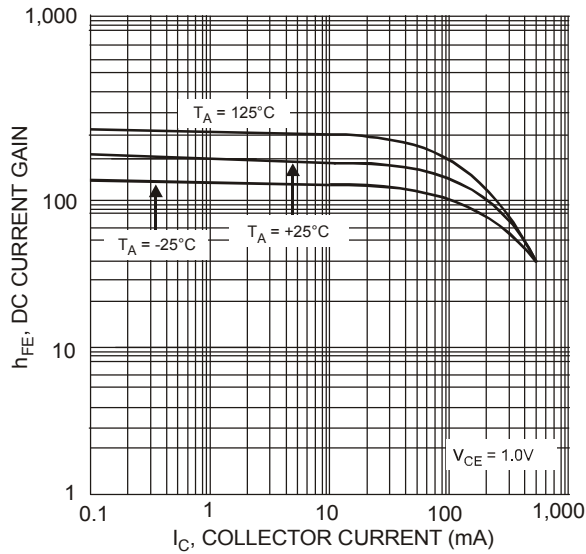


Fig. 3 Typical DC Current Gain vs. Collector Current (4401)

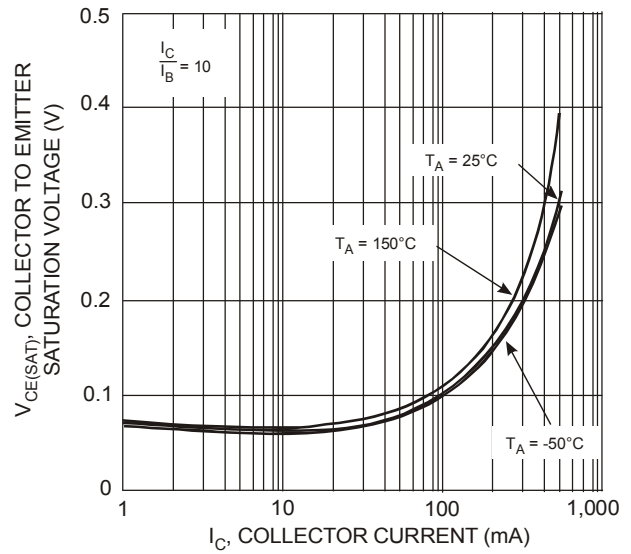


Fig. 4 Collector Emitter Saturation Voltage vs. Collector Current (4401)

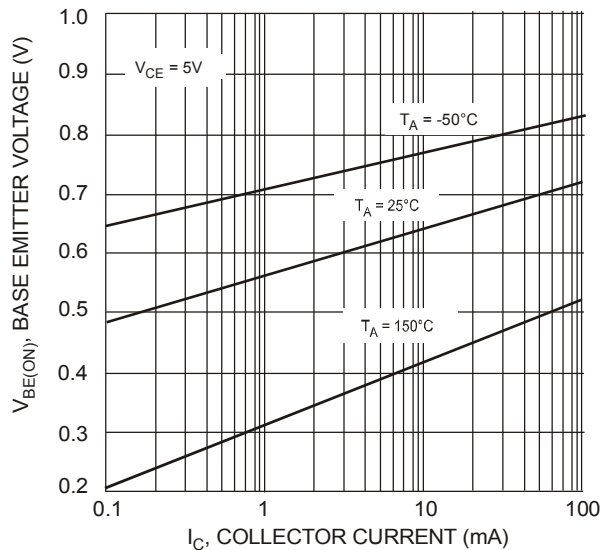


Fig. 5 Base Emitter Voltage vs. Collector Current (4401)

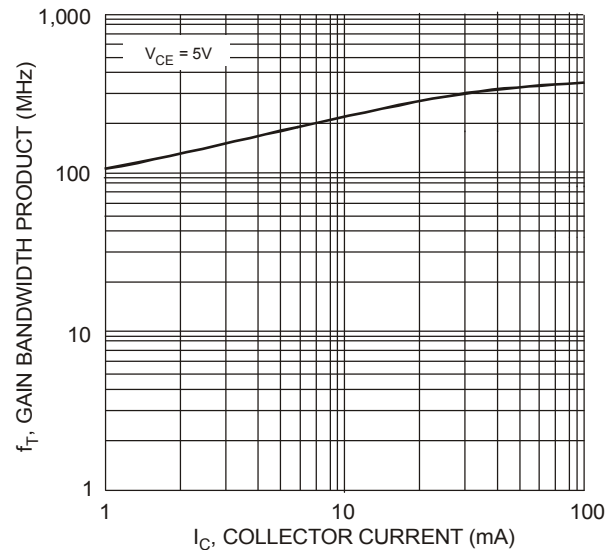


Fig. 6 Gain Bandwidth Product vs. Collector Current (4401)

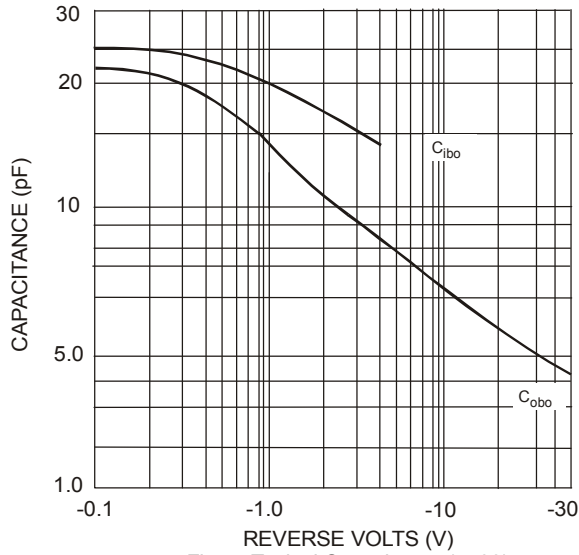


Fig. 7 Typical Capacitance (4403)

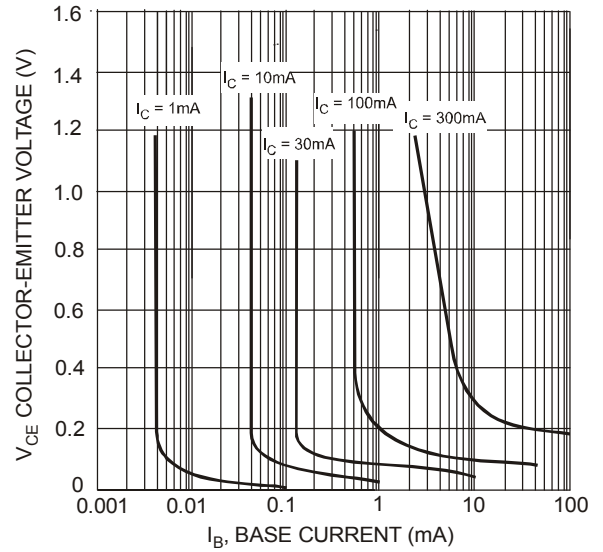


Fig. 8 Typical Collector Saturation Region (4403)

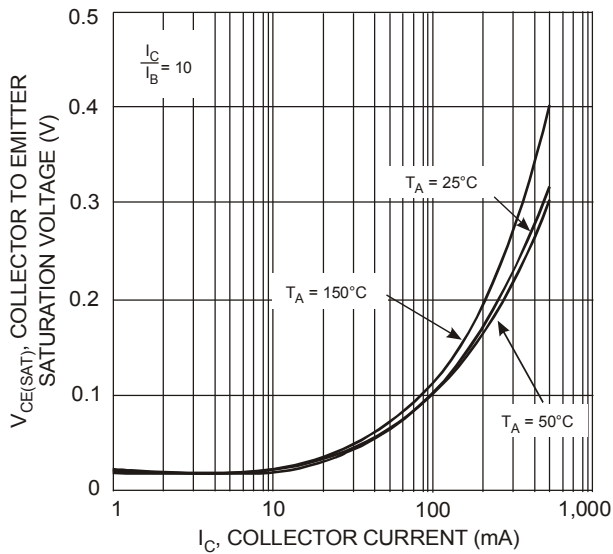


Fig. 9 Collector Emitter Saturation Voltage vs. Collector Current (4403)

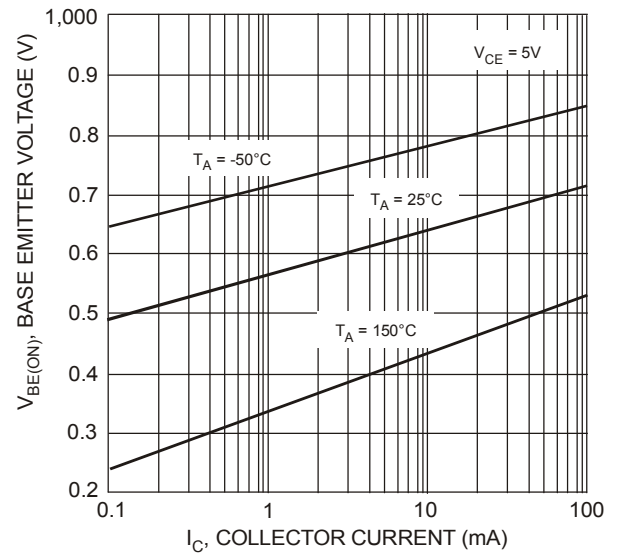


Fig. 10 Base-Emitter Voltage vs. Collector Current (4403)

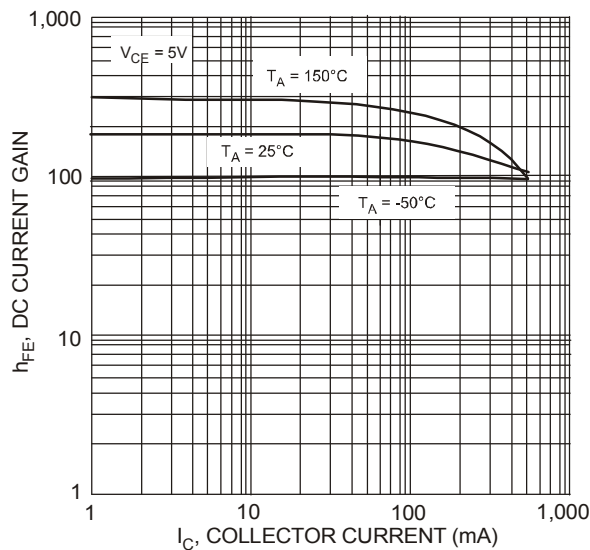


Fig. 11 DC Current Gain vs. Collector Current (4403)

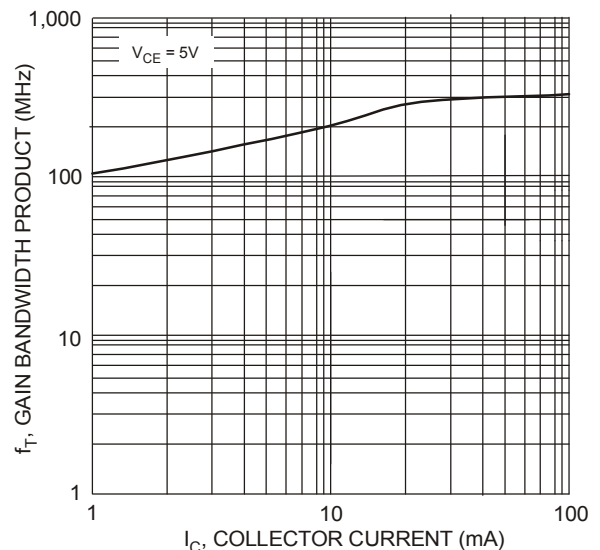


Fig. 12 Gain Bandwidth Product vs. Collector Current (4403)

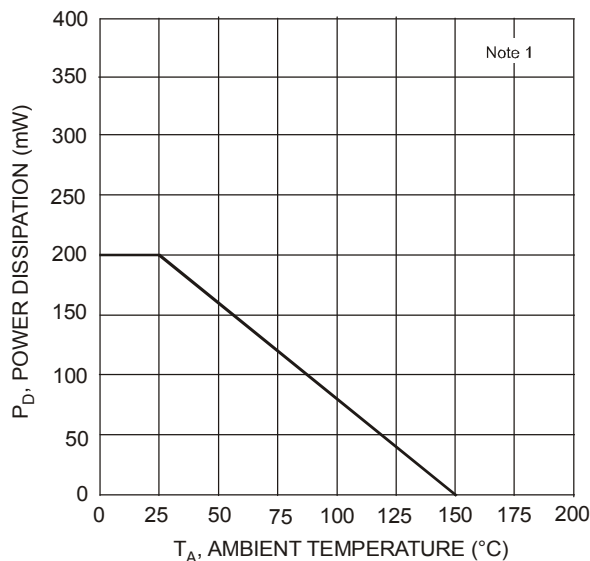


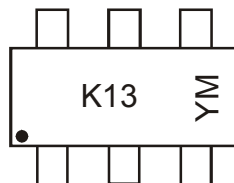
Fig. 13 Max Power Dissipation vs. Ambient Temperature (Total Device)

Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT4413-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K13 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Data Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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